

HRW0703A

Silicon Schottky Barrier Diode for Rectifying

HITACHI

Rev. 4
Nov. 1994

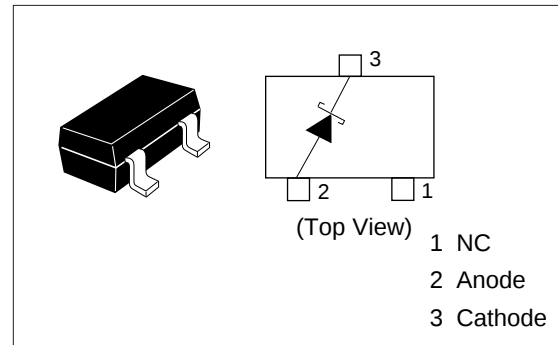
Features

- Low forward voltage drop and suitable for high efficiency rectifying.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HRW0703A	S 8	MPAK

Pin Arrangement



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}^*	30	V
Forward current	I_F^*	700	mA
Non-Repetitive peak forward surge current	I_{FSM}^{**}	5	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

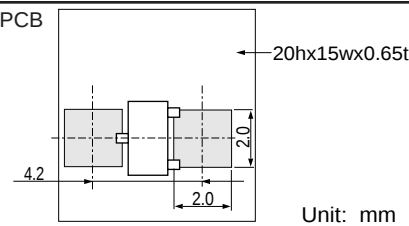
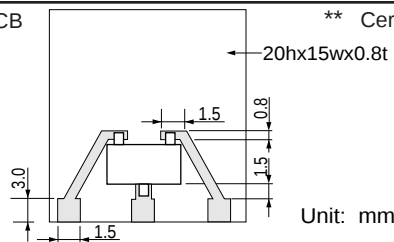
* See Fig.4 & Fig.5 ** 50Hz sine wave 1 pulse

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse current	I_R	—	—	100	μA	$V_R = 30 V$
Forward voltage	V_F	—	—	0.5	V	$I_F = 700 mA$
Capacitance	C	—	150	—	pF	$V_R = 0V, f = 1MHz$
Thermal resistance	$R_{th1(j-a)}$	—	390	—	°C/W	Polyimide substrate *
	$R_{th2(j-a)}$	—	290	—	°C/W	Ceramic substrate **

* Polyimide PCB

** Ceramic PCB



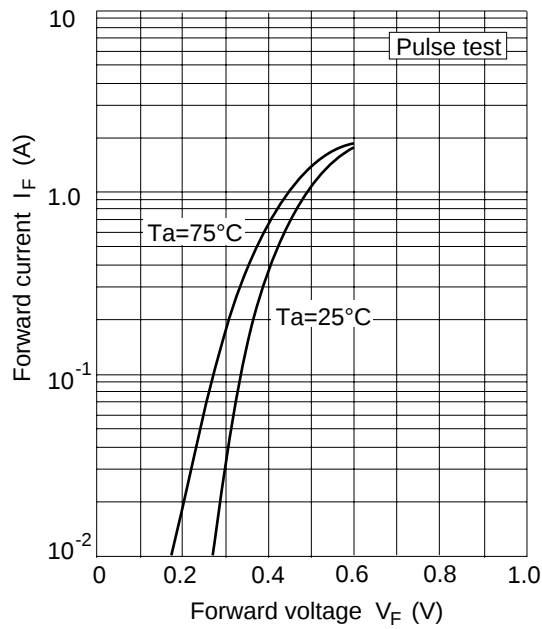


Fig.1 Forward current Vs. Forward voltage

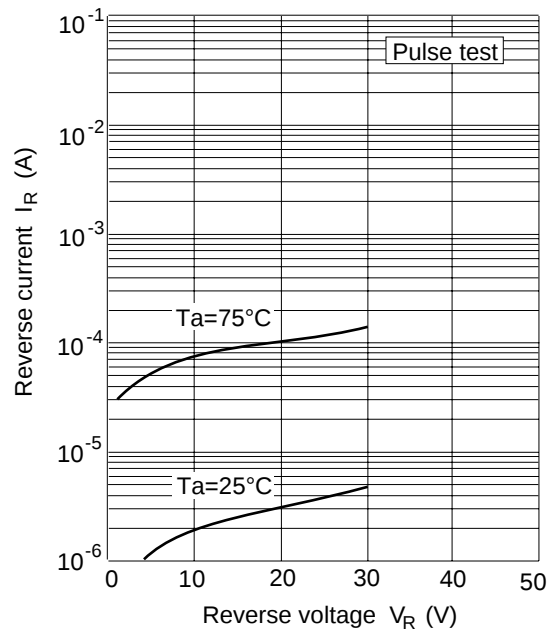


Fig.2 Reverse current Vs. Reverse voltage

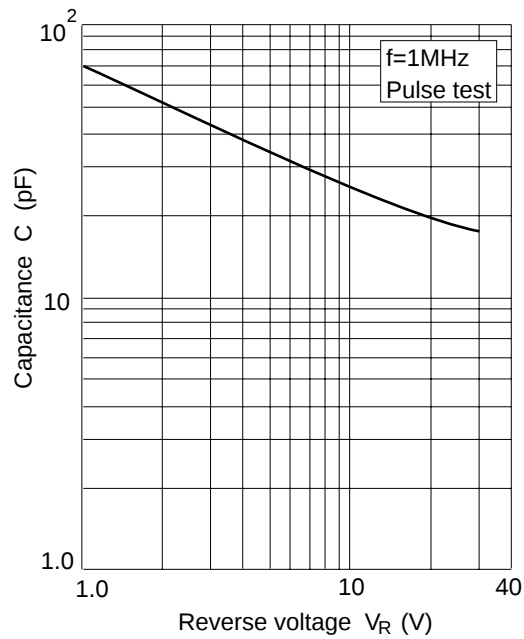


Fig.3 Capacitance Vs. Reverse voltage

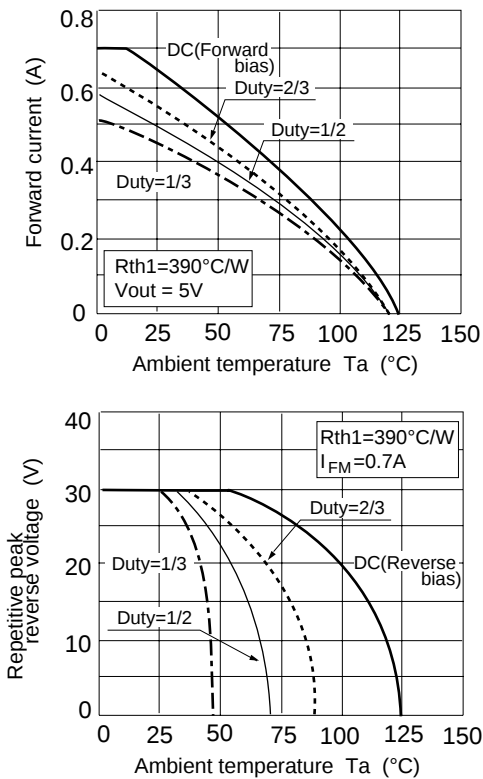


Fig.4 Forward current
Vs. Ambient temperature
(Polyimide substrate)

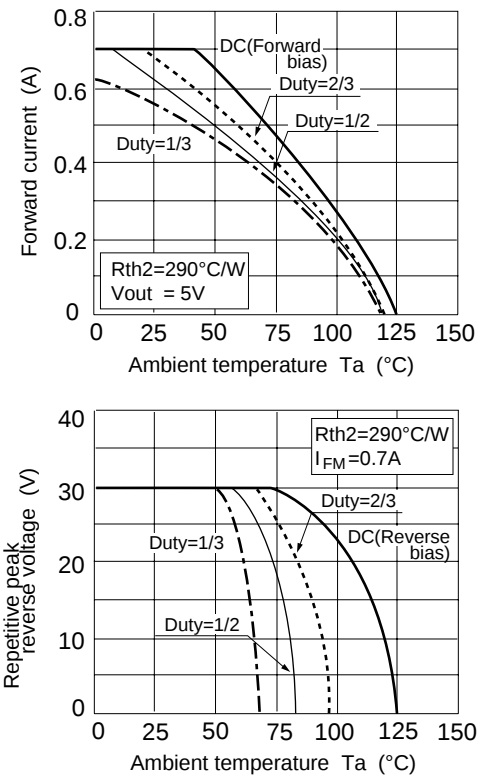
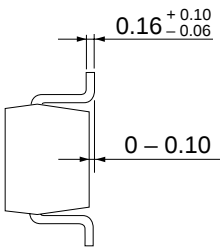
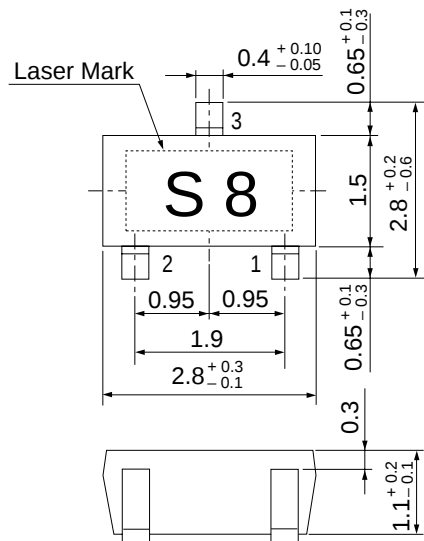


Fig.5 Repetitive peak reverse voltage
Vs. Ambient temperature
(Ceramic substrate)

Package Dimensions

Unit: mm



- 1 NC
- 2 Anode
- 3 Cathode

HITACHI Code	MPAK(1)
JEDEC Code	—
EIAJ Code	SC-59A
Weight (g)	0.011